

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
85V	11m Ω @10V	60A
	17m Ω @4.5V	

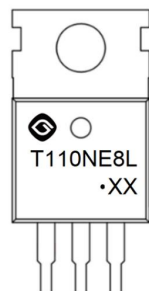
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

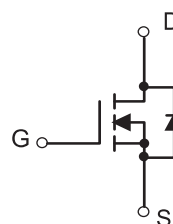
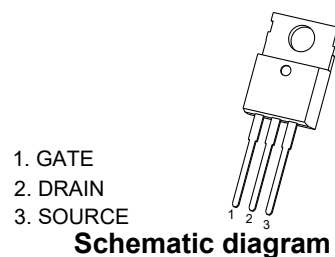
- Power Switching Application

MARKING:



T110NE8L = Device Code
 XX = Date Code
 Solid Dot = Green Indicator

TO-220-3L- C



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	85	V
Gate - Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	60	A
	$T_C = 100^\circ\text{C}$	I_D	39	A
Pulsed Drain Current ²		I_{DM}	240	A
Single Pulsed Avalanche Current ³		I_{AS}	22	A
Single Pulsed Avalanche Energy ³		E_{AS}	100	mJ
Power Dissipation ⁵		P_D	75	W
$T_C = 25^\circ\text{C}$				
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	52	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	1.67	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

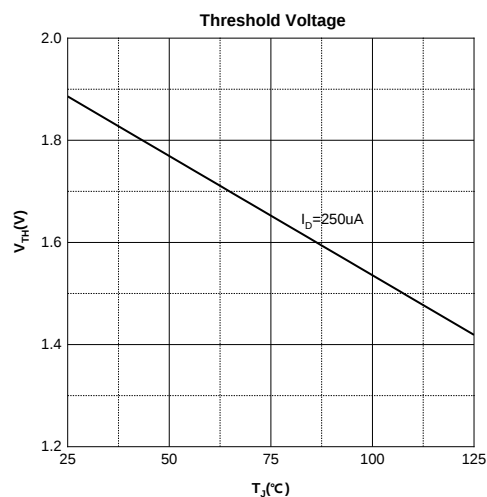
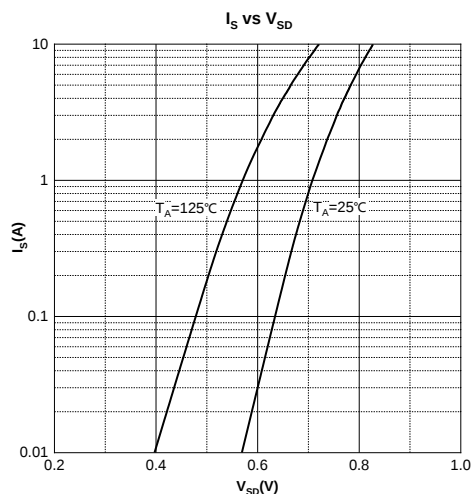
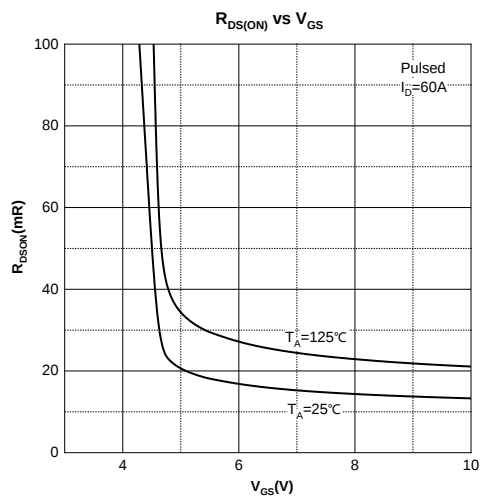
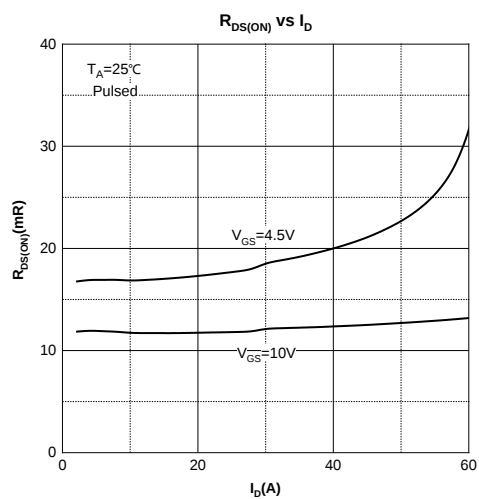
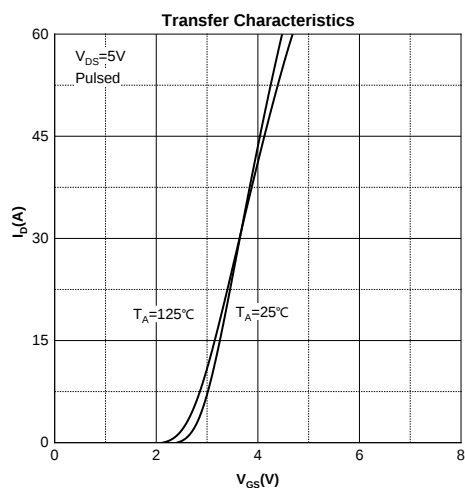
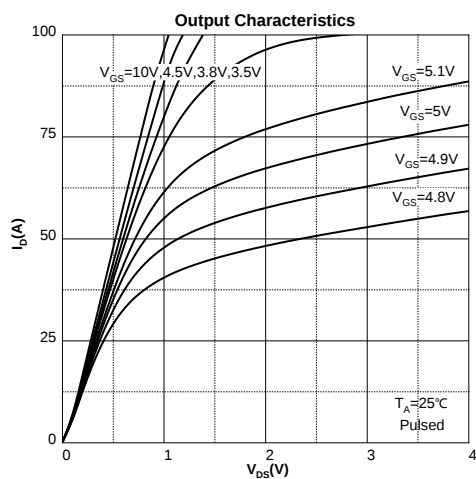
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

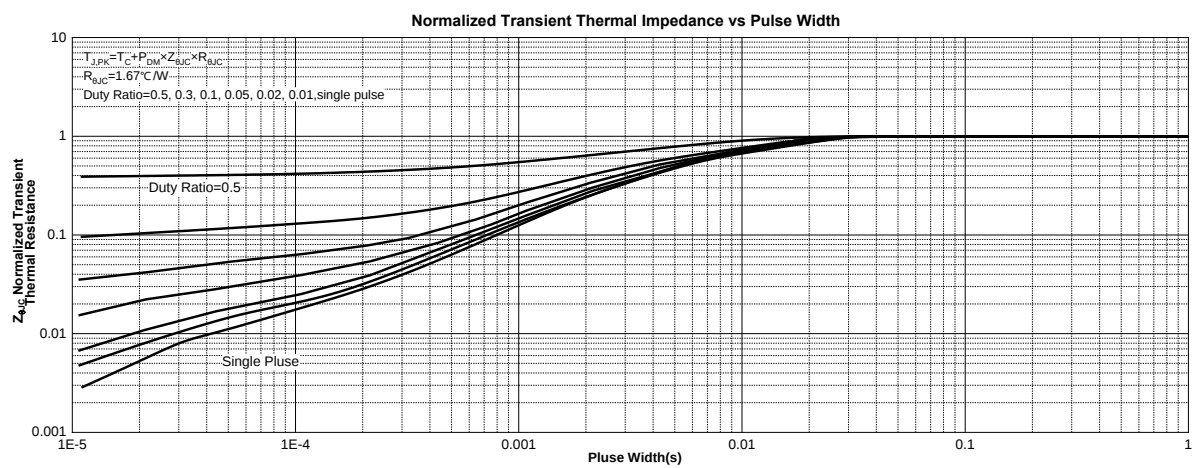
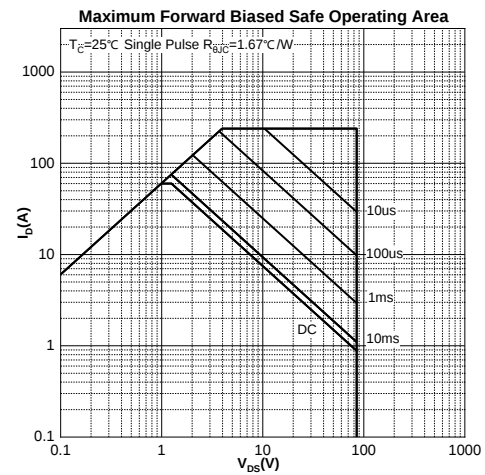
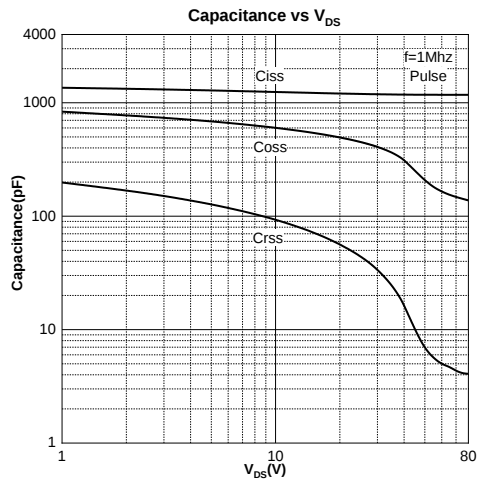
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	85			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 68V, V _{GS} = 0V			1	μA
Gate - Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	2.0	3.0	V
Drain-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 20A		11	14	mΩ
		V _{GS} = 4.5V, I _D = 10A		17	22	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 40V, V _{GS} = 0V, f = 1MHz		1177		pF
Output Capacitance	C _{oss}			315		
Reverse Transfer Capacitance	C _{rss}			17		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		2.4		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 60V, V _{GS} = 10V, I _D = 20A		21.4		nC
Gate-source Charge	Q _{gs}			4.7		
Gate-drain Charge	Q _{gd}			5.0		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 40V, V _{GS} = 10V, I _D = 50A, R _G = 6Ω		12		ns
Turn-on Rise Time	t _r			13		
Turn-off Delay Time	t _{d(off)}			16		
Turn-off Fall Time	t _f			5		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 10A			1.2	V

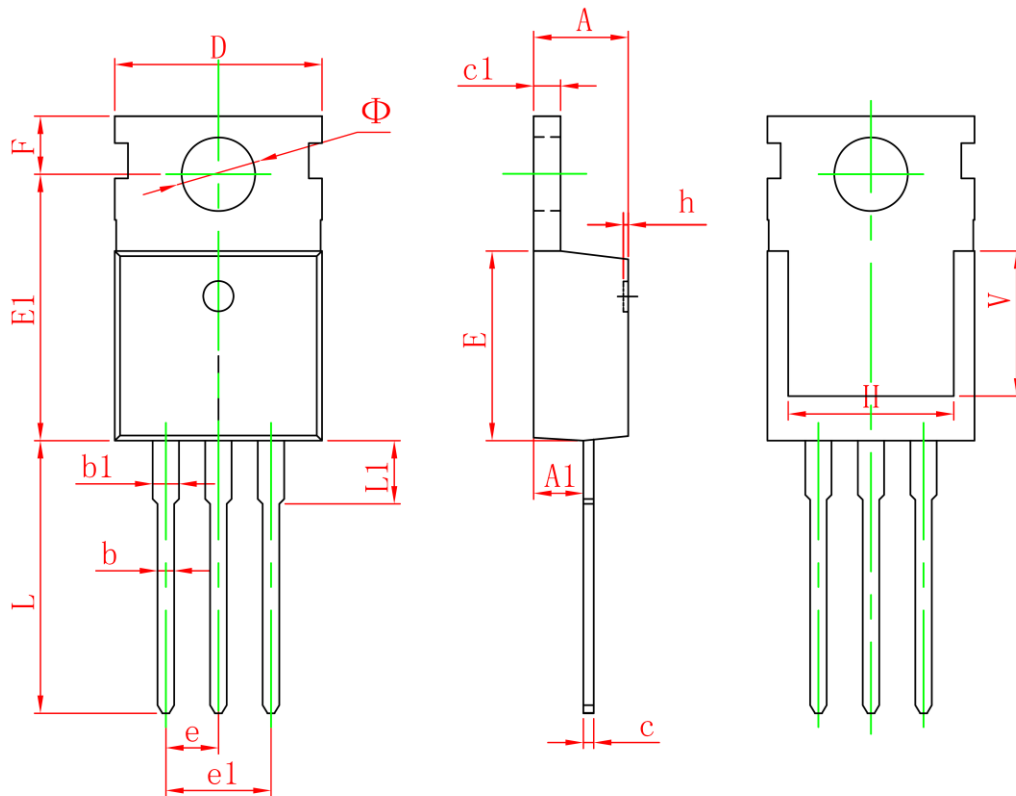
Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 40V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics





TO-220-3L-C Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540TYP		0.100TYP	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900REF		0.272REF	
Φ	3.400	3.800	0.134	0.150